Product data sheet

1. Product profile

1.1 General description

Planar passivated sensitive gate four quadrant triac in a SOT223 (SC-73) surface-mountable plastic package intended for applications requiring enhanced immunity to noise and direct interfacing to logic level ICs and low power gate drivers.

1.2 Features and benefits

- Direct interfacing to logic level ICs
- Enhanced current surge capability
- Enhanced noise immunity
- High blocking voltage capability
- Sensitive gate triggering in all four quadrants
- Surface-mountable package

1.3 Applications

- General purpose low power motor control
- Home appliances

- Industrial process control
- Low power AC Fan controllers

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	-	12.5	Α
I _{T(RMS)}	RMS on-state current	full sine wave; T _{sp} ≤ 103 °C; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	1	Α



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Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
l _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ C; }}$	0.3	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 9}}{}$	0.3	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{\text{Im}}$	0.3	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G+};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{\text{ or } 100 \text{ Figure 9}}$	0.3	-	7	mA

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		N.I.
2	T2	main terminal 2	4	T2—
3	G	gate		`G sym051
4	T2	main terminal 2		
			SOT223 (SOT223)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
Z0107MN0	SOT223	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
Z0107MN0	107MN0

[1] % = placeholder for manufacturing site code

0107MN0

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 103 ^{\circ}\text{C}$; see Figure 3; see Figure 1; see Figure 2	-	1	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 20 \text{ms}$; see Figure 4; see Figure 5	-	12.5	Α
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	13.8	Α
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	0.78	A ² s
dI _T /dt	rate of rise of on-state current	I_T = 1 A; I_G = 20 mA; dI_G/dt = 100 mA/ μ s; T2+ G+	-	50	A/µs
		I_T = 1 A; I_G = 20 mA; dI_G/dt = 100 mA/ μ s; T2+ G-	-	50	A/µs
		I_T = 1 A; I_G = 20 mA; dI_G/dt = 100 mA/ μ s; T2- G-	-	50	A/µs
		I_T = 1 A; I_G = 20 mA; dI_G/dt = 100 mA/ μ s; T2- G+	-	20	A/µs
I _{GM}	peak gate current		-	1	Α
P _{GM}	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

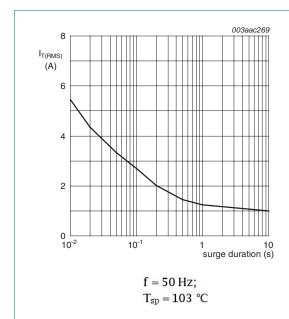


Fig 1. RMS on-state current as a function of surge duration; maximum values

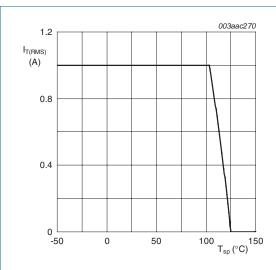
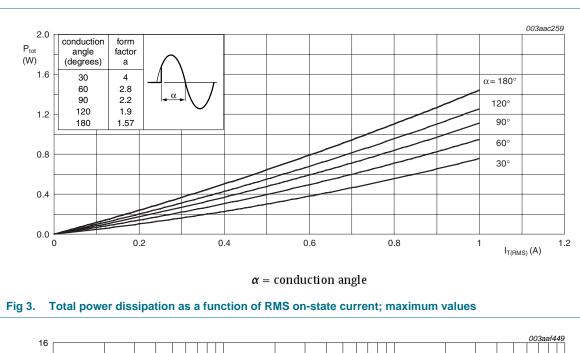


Fig 2. RMS on-state current as a function of solder point temperature; maximum values

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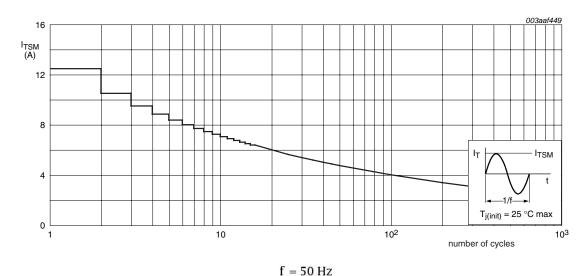
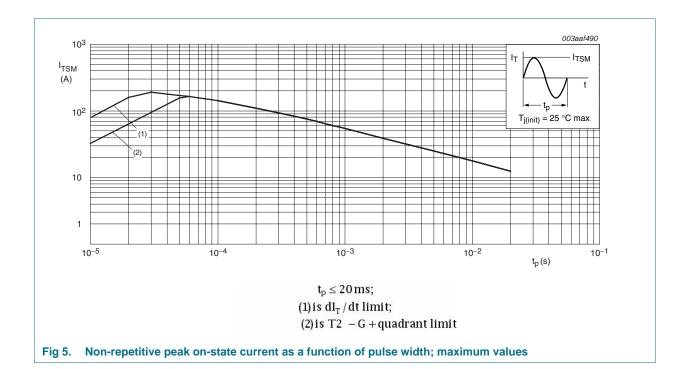


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

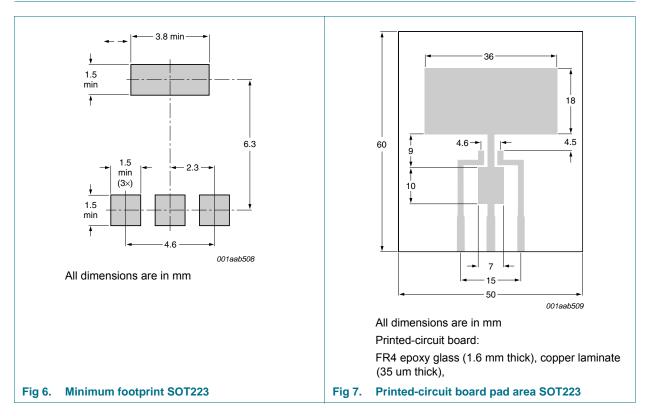


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6. Thermal characteristics

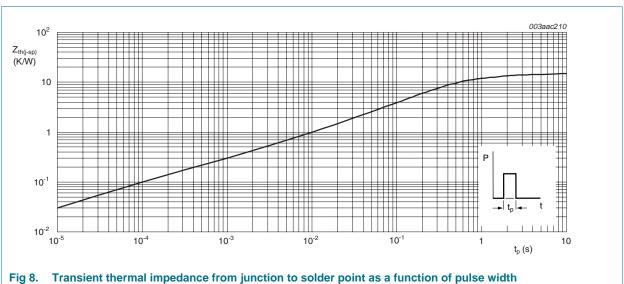
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	full cycle; see Figure 8	-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air; printed-circuit board mounted: minimum footprint; full cycle; see Figure 6	-	156	-	K/W
		in free air; printed-circuit board mounted: pad area; full cycle; see Figure 7	-	70	-	K/W



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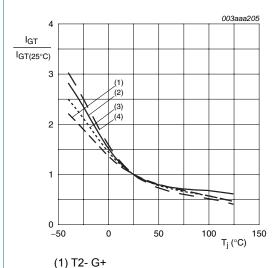
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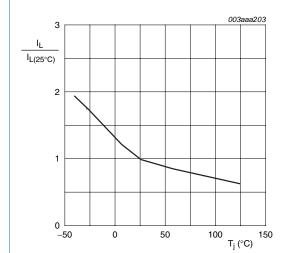


7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
-	racteristics	Conditions	.,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	.,,,,	Max	Oilie
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; see <u>Figure 9</u>	0.3	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G -; $ $T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ or } 100 \text{ cm}}$	0.3	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G-;} $ $T_j = 25 \text{ °C; see } \frac{\text{Figure 9}}{\text{ Figure 9}}$	0.3	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+; T_j = 25 °C; see Figure 9$	0.3	-	7	mA
L	latching current	$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure } 10}{\text{ III}}$	-	-	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{}$	-	-	25	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure } 10}{\text{ Figure } 10}$	-	-	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{}$	-	-	10	mA
Н	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 14</u>	-	-	10	mA
√ _T	on-state voltage	$I_T = 1 A$; $T_j = 25 °C$; see Figure 11	-	1.3	1.6	V
/ _{GT}	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure } 12}{\text{ c}}$	-	-	1.3	V
		$V_D = 600 \text{ V}; I_T = 0.1 \text{ A};$ $T_j = 125 \text{ °C}$	0.2	-	-	V
l _D	off-state current	V _D = 600 V; T _j = 125 °C	-	-	0.5	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 110 °C; gate open circuit; exponential waveform; see Figure 13	100	-	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	V_D = 400 V; T_j = 110 °C; dI_{com}/dt = 0.44 A/ms; gate open circuit	0.5	-	-	V/µs

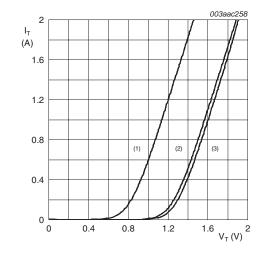


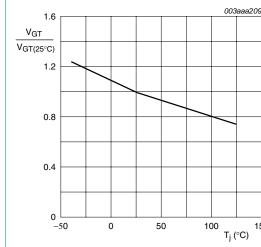


- (1) 12- 61
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig 9. Normalized gate trigger current as a function of junction temperature

Fig 10. Normalized latching current as a function of junction temperature





 $V_0 = 1.254 \text{ V}$

 $R_s = 0.31 \Omega$

(1) T_j = 125 °C; typical values

(2) $T_j = 125$ °C; maximum values

(3) T_i = 25 °C; maximum values

Fig 11. On-state current as a function of on-state voltage

Fig 12. Normalized gate trigger voltage as a function of junction temperature

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Product data sheet



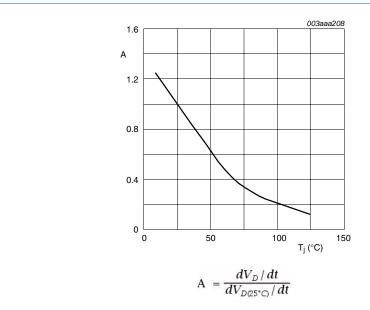


Fig 13. Normalized critical rate of rise of off-state voltage as a function of junction temperature; typical values

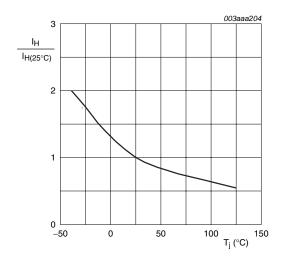


Fig 14. Normalized holding current as a function of junction temperature

8. Package outline

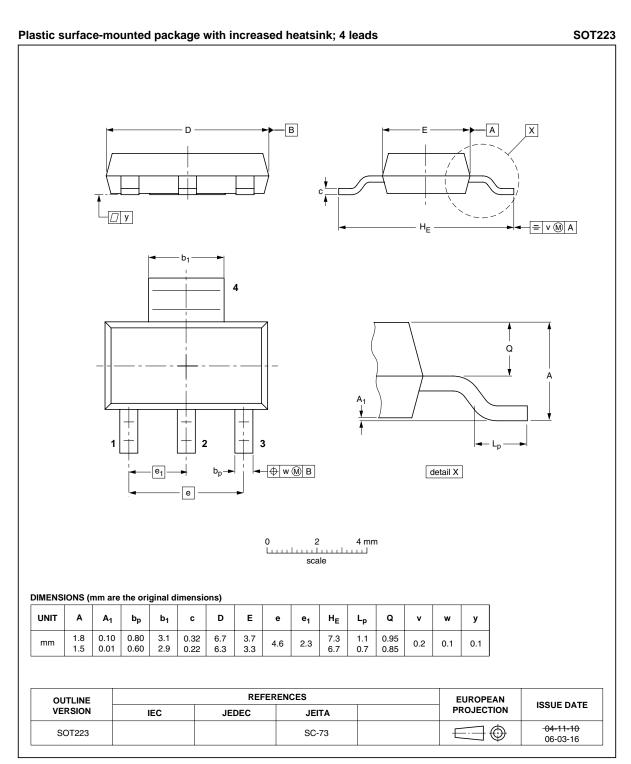
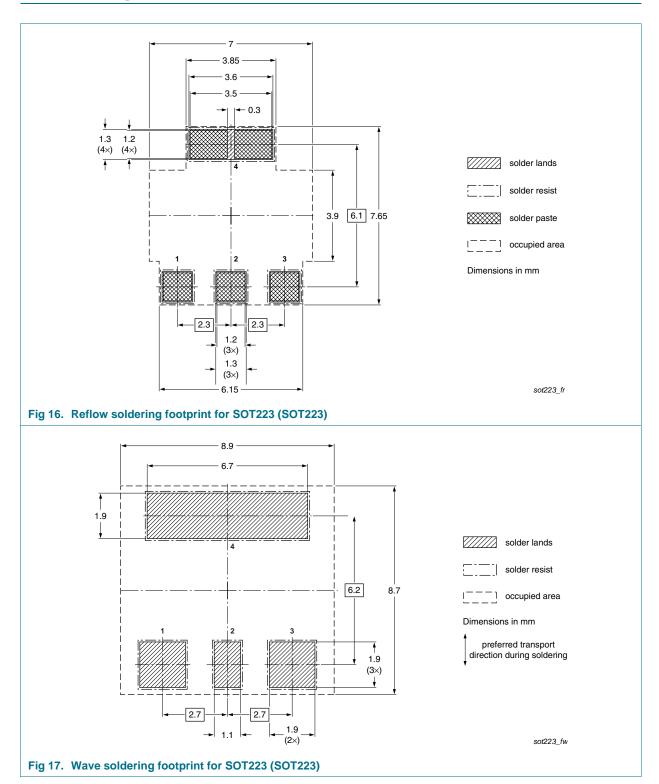


Fig 15. Package outline SOT223 (SOT223)

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9. Soldering



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10. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
Z0107MN0 v.1	20110103	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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